

General Description

The WSD20100DN56 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSD20100DN56 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

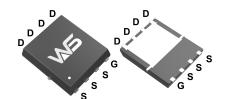
Product Summery

BVDSS	RDSON	ID
20V	1.6mΩ	90A

Applications

- Switch
- Power System
- Load Switch

DFN5X6-8 Pin Configuration





Absolute Maximum Ratings (Tc=25℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
Vos	Drain-Source Voltage	20	V
Vgs	Gate-Source Voltage	±12	V
In@Tc=25°C	Continuous Drain Current	90	А
In@Tc=100°C	Continuous Drain Current	48	А
Ідм	Pulsed Drain Current2	270	А
Eas	Single Pulse Avalanche Energy ₃	80	mJ
las	Avalanche Current	40	A
P ⊅@Tc=25°C	Total Power Dissipation4	83	W
Тѕтс	Storage Temperature Range	-55 to 150	$^{\circ}$ C
TJ	Operating Junction Temperature Range	-55 to 150	$^{\circ}$
Reja	Thermal Resistance Junction-ambient ₁(t ≤ 10S)	20	°C/W
Reja	Thermal Resistance Junction-ambient ₁ (Steady State)	55	°C/W
Rejc	Thermal Resistance Junction-case 1	1.5	°C/W



Electrical Characteristics (Tc=25℃unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	Vgs=0V , Ip=250uA	20	23		V
V _{GS(th)}	Gate Threshold Voltage	Vgs=Vps, Ip=250uA	0.5	0.68	1.0	V
RDS(ON)	Static Drain-Source On-Resistance2	V _G s=10V , I _D =20A		1.6	2.0	mΩ
RDS(ON)	Static Drain-Source On-Resistance2	Vgs=4.5V , ID=20A		1.9	2.5	mΩ
RDS(ON)	Static Drain-Source On-Resistance2	V _{GS} =2.5V , I _D =20A		2.8	3.8	mΩ
	Drain-Source Leakage Current	V _{DS} =16V , V _{GS} =0V , T _J =25℃			1	- uA
Ipss		V _{DS} =16V , V _{GS} =0V , T _J =125℃			5	
Igss	Gate-Source Leakage Current	V _{GS} =±10V , V _{DS} =0V			±10	uA
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.2		Ω
Qg	Total Gate Charge (10V)			77		nC
Qgs	Gate-Source Charge	V _{DS} =15V , V _{GS} =10V , I _D =20A		8.7		
Qgd	Gate-Drain Charge			14		
Td(on)	Turn-On Delay Time			10.2		ns
Tr	Rise Time	V _{DD} =15V , V _{GS} =10V , R _G =3 ,		11.7		
Td(off)	Turn-Off Delay Time	lp=20A		56.4		
Tf	Fall Time			16.2		
Ciss	Input Capacitance	V _{DS} =10V , V _{GS} =0V , f=1MHz		4307		
Coss	Output Capacitance			501		pF
Crss	Reverse Transfer Capacitance			321		
IS	Continuous Source Current _{1,5}	V _G =V _D =0V , Force Current			50	Α
VsD	Diode Forward Voltage ₂	Vgs=0V , Is=1A , Tյ=25℃			1.2	V
trr	Reverse Recovery Time	IF=20A , di/dt=100A/μs ,		22		nS
Qrr	Reverse Recovery Charge	TJ=25℃		72		nC

Note:

- 1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
- 2_{\times} The data tested by pulsed , pulse width \leqq 300us , duty cycle \leqq 2%
- $3\sqrt{1000}$ The EAS data shows Max. rating . The test condition is VDD=16V,VGS=10V,L=0.1mH,IAS=39A
- 4. The power dissipation is limited by 175°C junction temperature
- 5. The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation.



Typical Characteristics

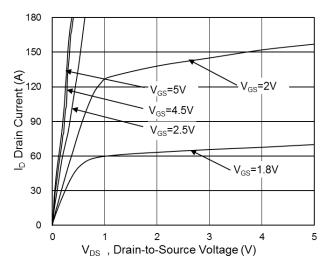


Fig.1 Typical Output Characteristics

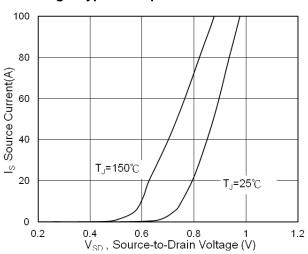


Fig.3 Forward Characteristics of Reverse

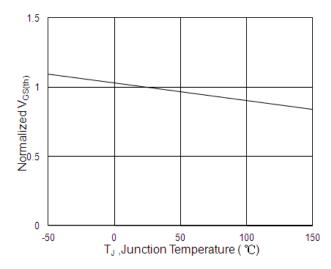


Fig.5 Normalized $V_{\text{GS(th)}}$ vs. T_{J}

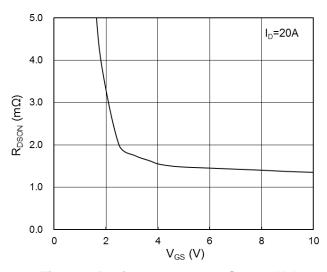


Fig.2 On-Resistance vs. Gate-Source Voltage

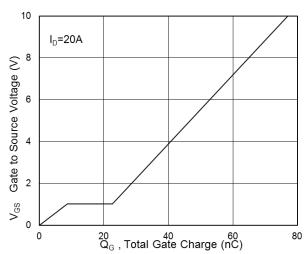


Fig.4 Gate-Charge Characteristics

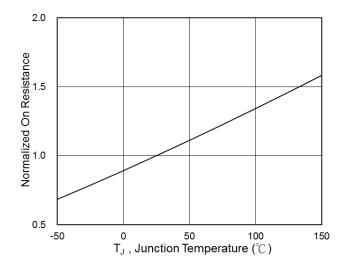
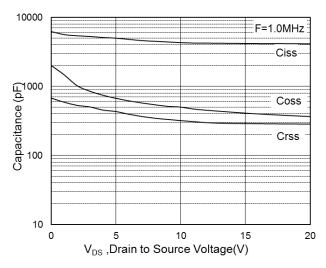


Fig.6 Normalized R_{DSON} vs. T_J





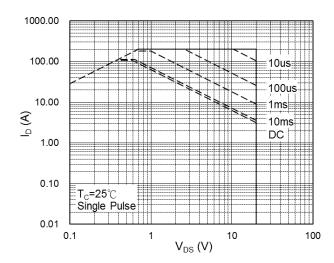


Fig.7 Capacitance

Fig.8 Safe Operating Area

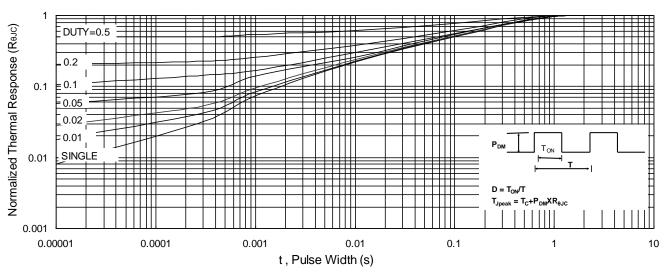


Fig.9 Normalized Maximum Transient Thermal Impedance

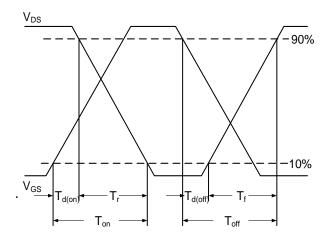


Fig.10 Switching Time Waveform

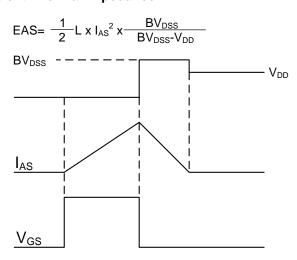


Fig.11 Unclamped Inductive Switching Waveform



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